

Inner workings of the 120⁰C baking effect studied by positron annihilation

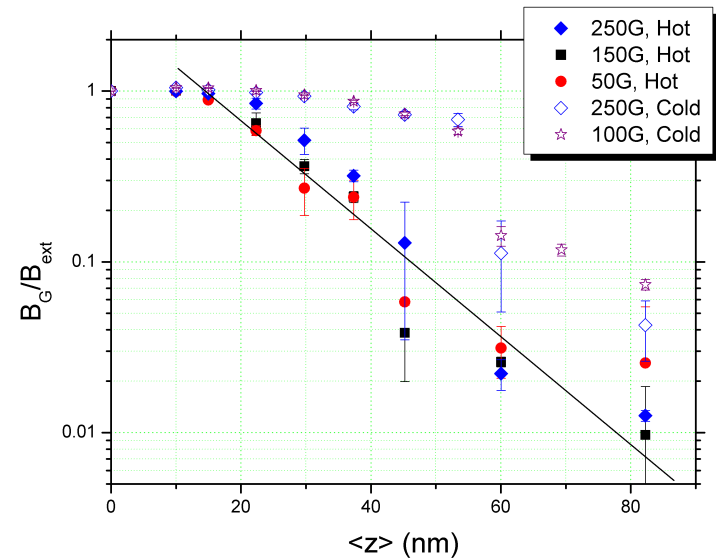
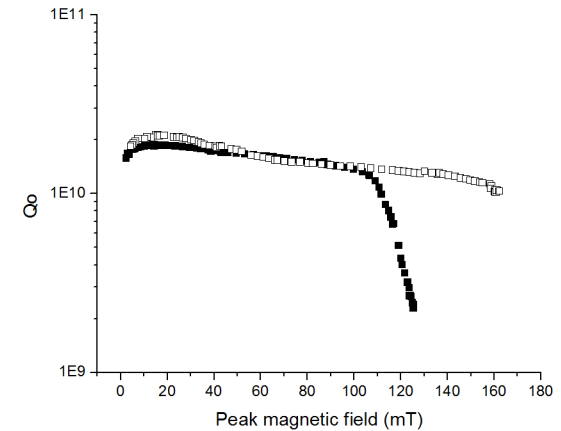
A. Romanenko

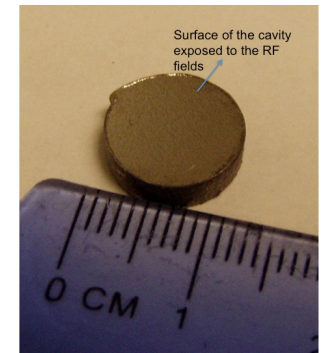
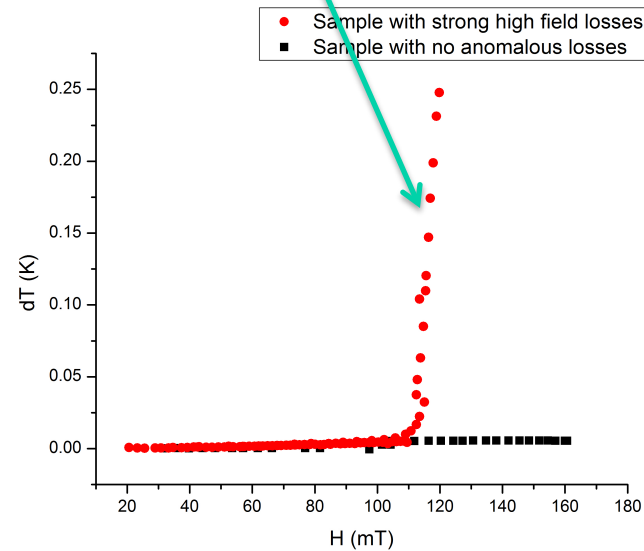
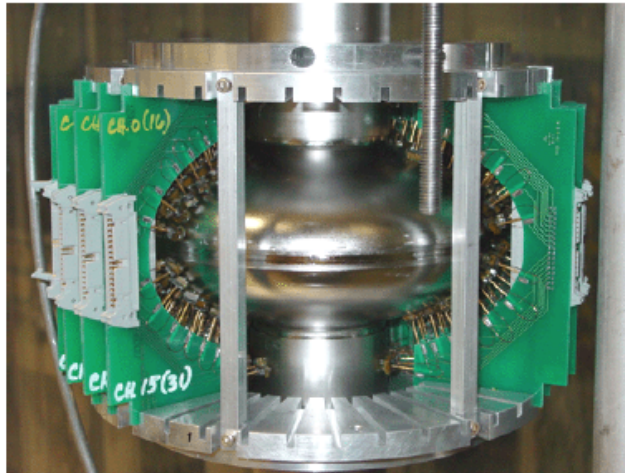
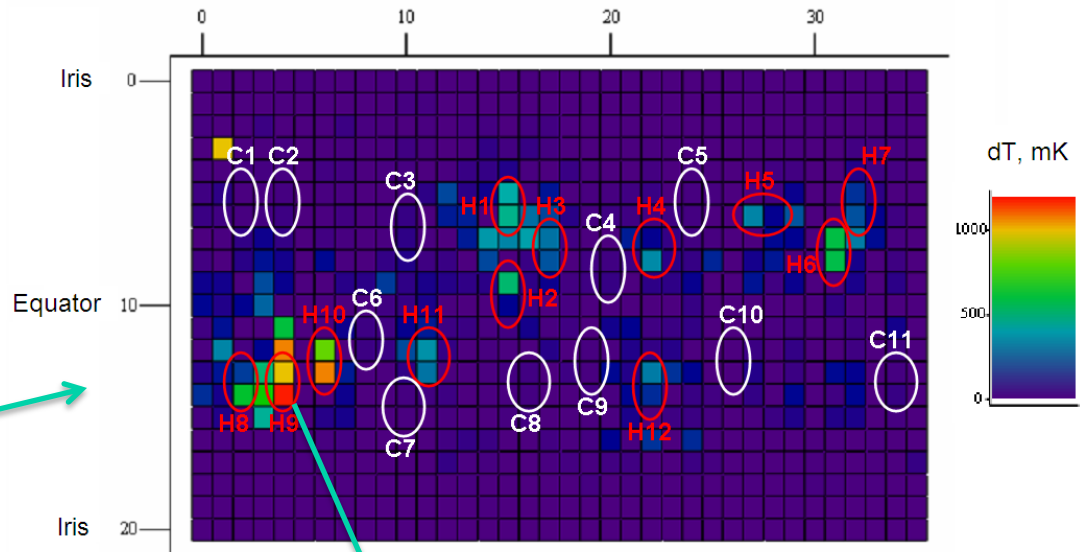
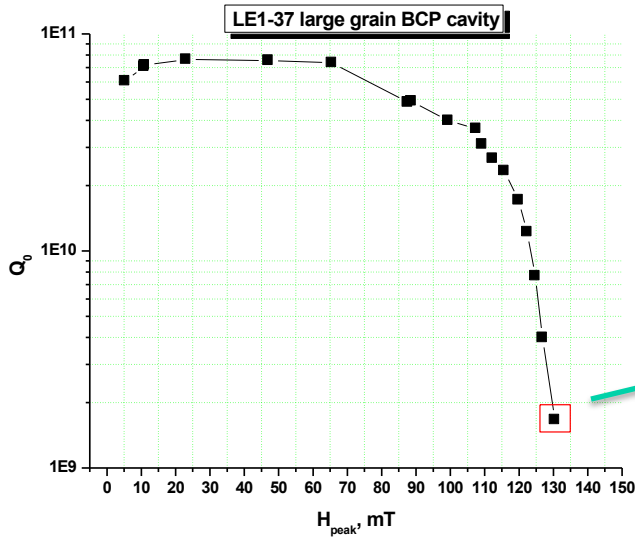
Fermilab, USA

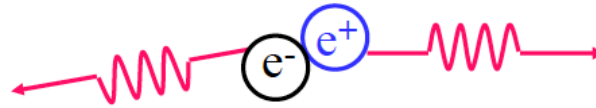
C. Edwardson, P. Coleman

University of Bath, UK

- Applied to consistently remove the high field Q-slope in EP/large grain BCP cavities
- Lowers electron m.f.p. as deduced from fits to $R_s(T)$ using BCS framework
- Drastically modifies near-surface order parameter as observed in μ SR
- Effect on BCS surface resistance extends to $>\sim 300$ nm deep
- Effect on HFQS can be eliminated by ~ 20 nm material removal

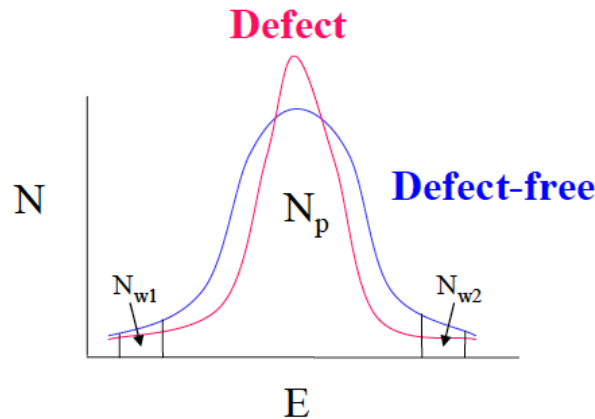






γ -ray ($511\text{keV} \pm \Delta E$)

Doppler Broadening



$$S = N_p / N_{\text{total}}$$

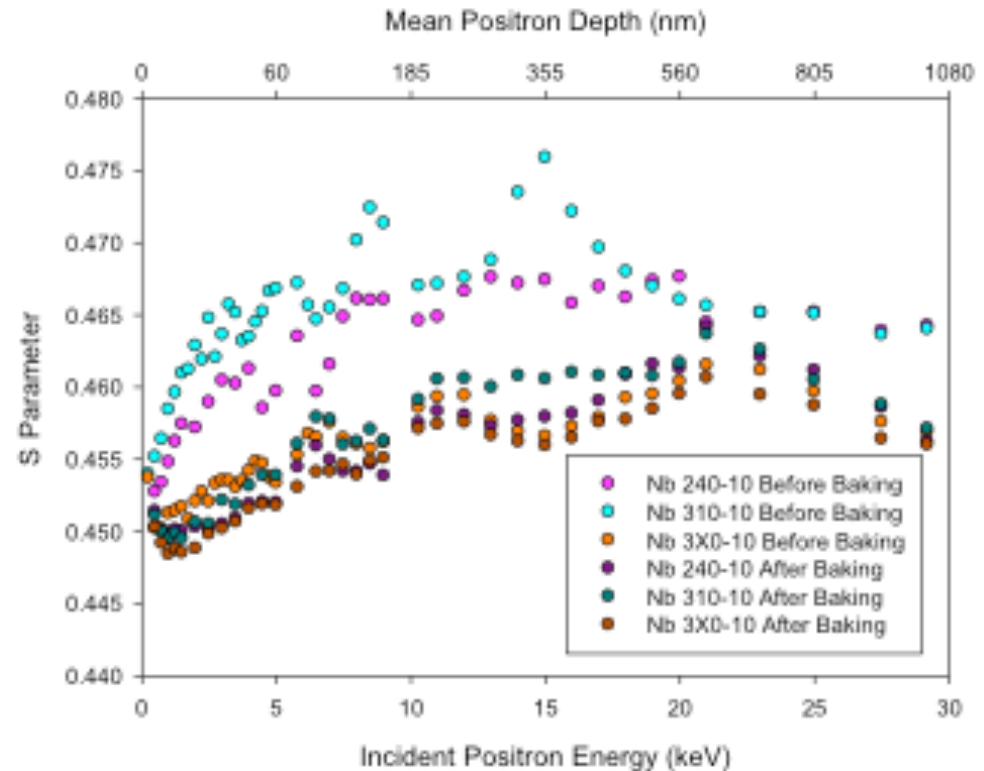
$$S_{\text{defect}} > S_{\text{defect-free}}$$

$$W = (N_{w1} + N_{w2}) / N_{\text{total}}$$

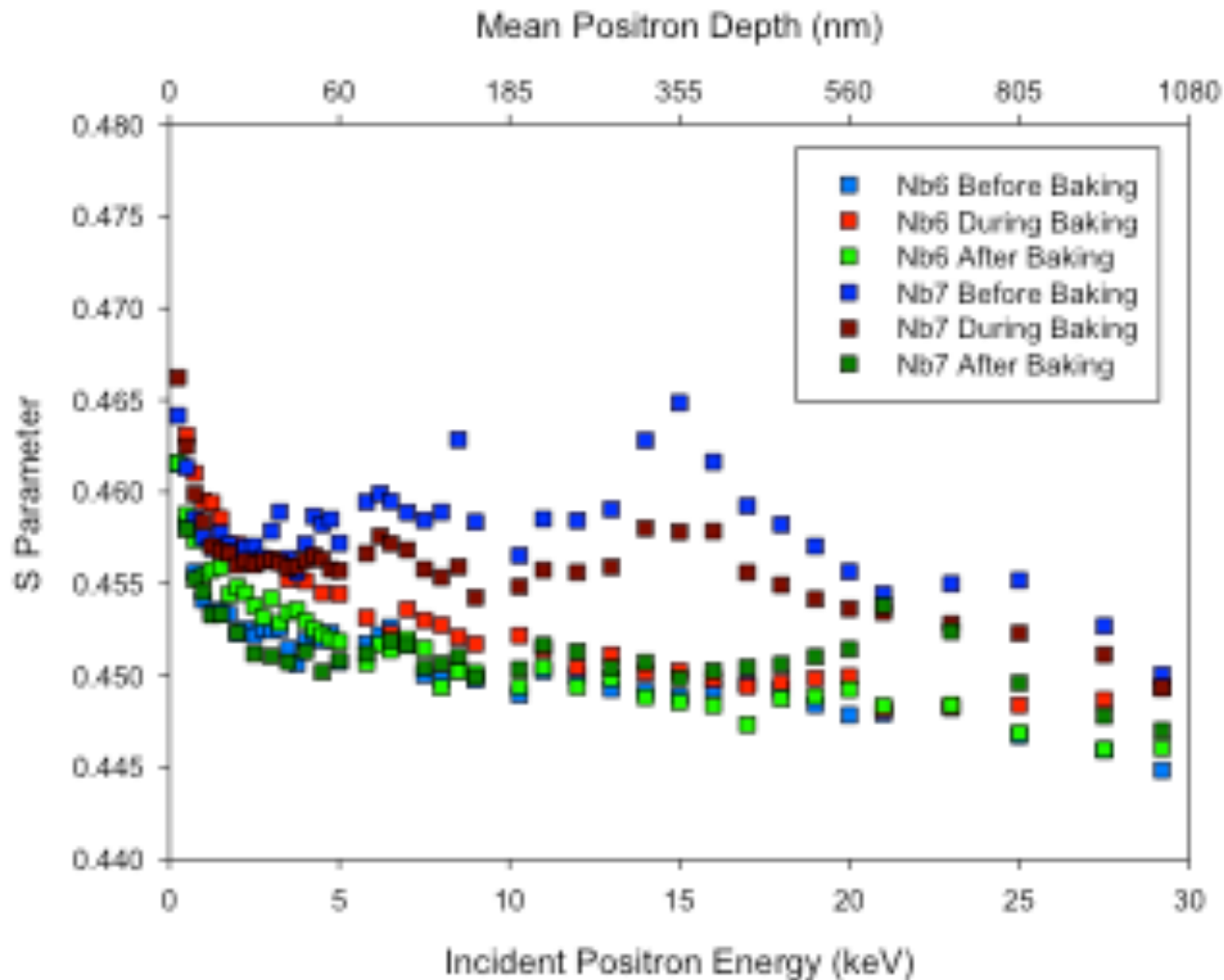
- S parameter corresponds to positron annihilation with valence electrons, W \rightarrow core electrons
- S is sensitive to open-volume defects, W to chemical surrounding at the annihilation site
- Increase in S parameter indicates presence of vacancy defects

- Change positron energy E \rightarrow change stopping depth
- Measure $S(E)$, $W(E)$ \rightarrow depth profile of vacancies

- High concentration of vacancies in hot and “cold” spots
 - Consistent with $\sim 10^{-3}$ at. %
 - Difference due to the presence of peaks at particular depths?
- Baking decreases vacancy concentration significantly
 - Same depth profiles after 120C for all 3 samples

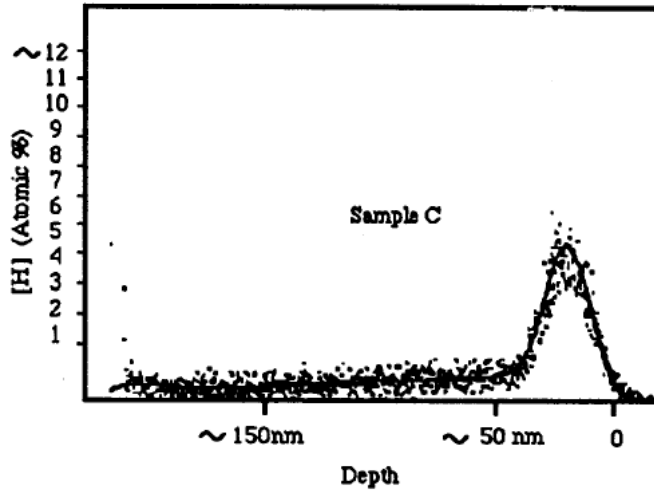


310-10 -> Hot spot with strong HFQS losses
 240-10 -> “Cold” spot with less HFQS losses
 3X0-10 -> No HFQS losses spot from baked cavity

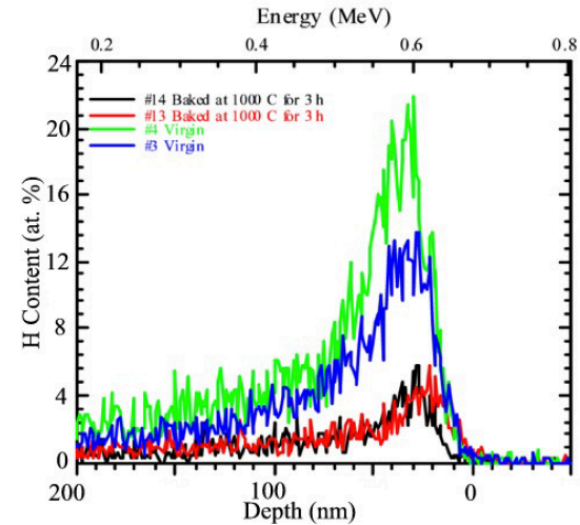


- Vacancies can be formed in concentrations by far (30 orders of magnitude) exceeding thermodynamic equilibrium
 - Enabled by the presence of interstitial H and can happen during: chemical treatments, furnace treatments
- Discovered in 1993
 - Y. Fukai and N. Okuma: Jpn. J. Appl. Phys. Vol. 32 (1993)
 - Phys. Rev. Lett. Vol. 73 (1994)
 - Since then found in many M-H systems including niobium!

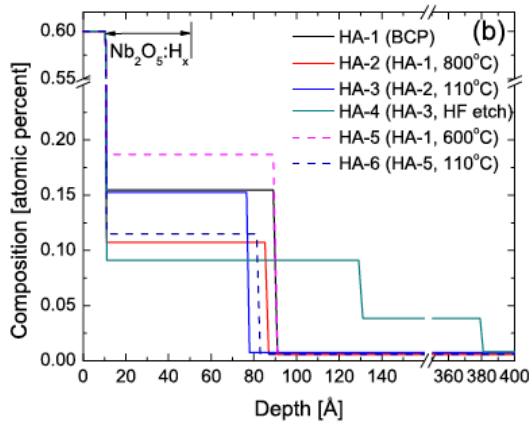
C. Antoine et al, SRF'91



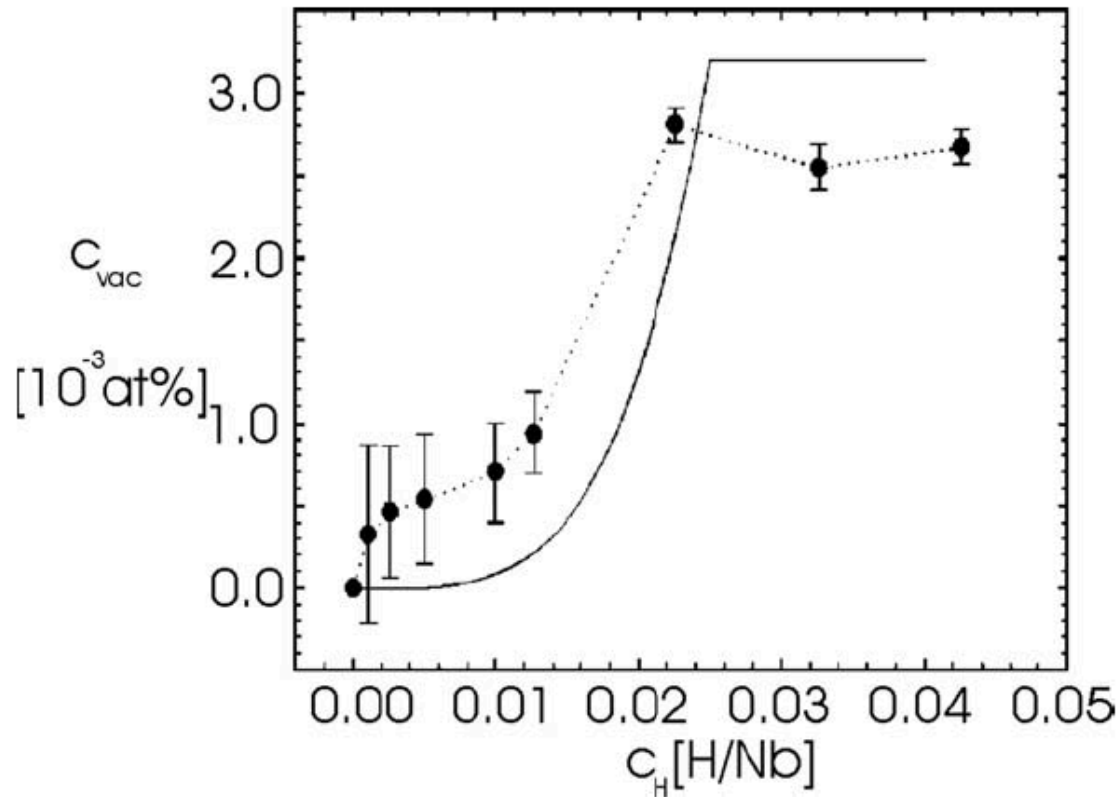
T. Tajima et al, SRF'03,



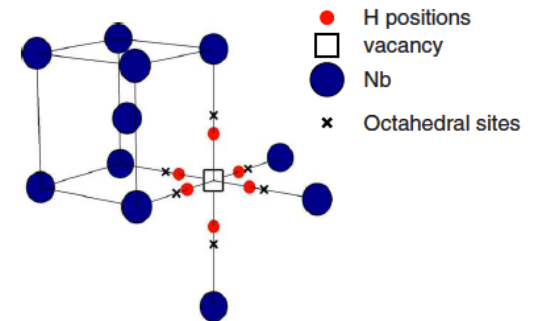
A. Romanenko and L. V. Goncharova, Supercond. Sci. Tech. 24 (2011) 105017



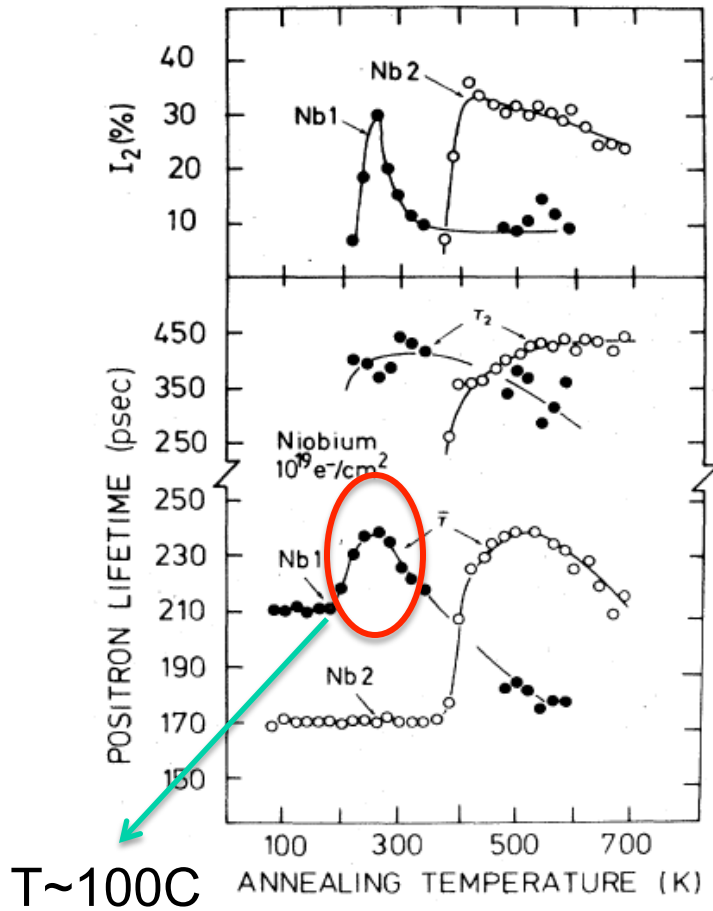
There exists a hydrogen-rich layer within the first several 10s of nms, which is NOT removed even after furnace treatment



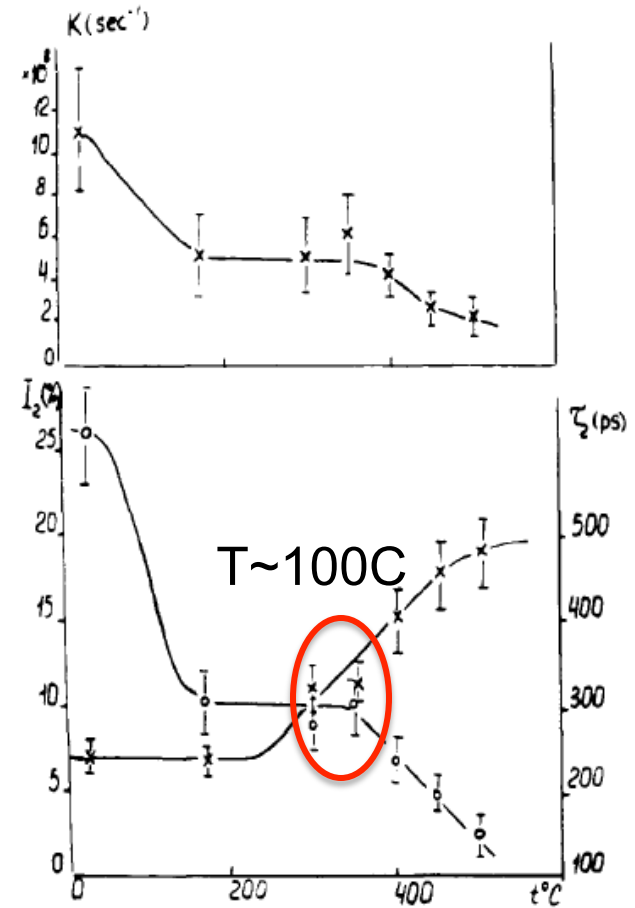
Cizek et al,
 Journal of Alloys and Compounds
 404–406 (2005) 580–583
 Cizek et al, PRB, 79, 074108
 (2009)



29 orders of magnitude higher concentration of vacancies possible in the presence of hydrogen as compared to thermal equilibrium

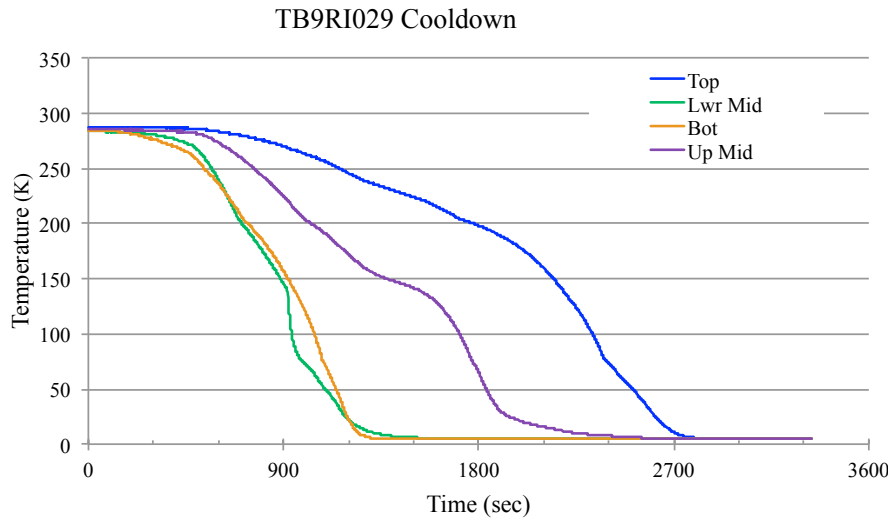


P. Hautojarvi et al, Phys. Rev. B,
Vol. 32, Num. 7, 1985



O. K. Alekseeva et al,
Physica Scripta. Vol. 20, 683-684,
1979

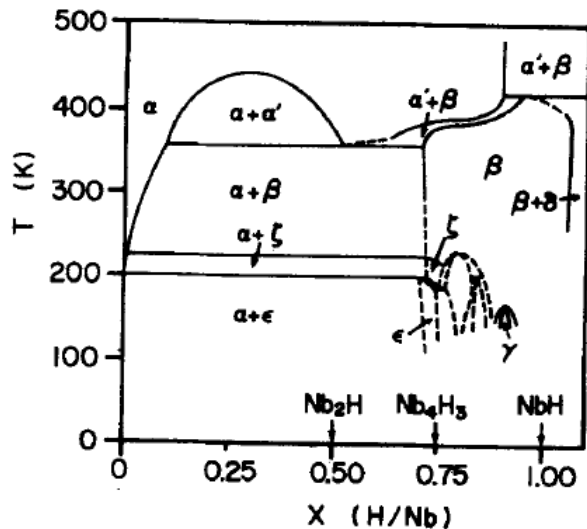
Typical fast cooldown of a cavity (FNAL)



Integrate the H diffusion over the time spent in the precipitation temperature range $T < 150\text{K} \Rightarrow L > 1 \text{ um}$



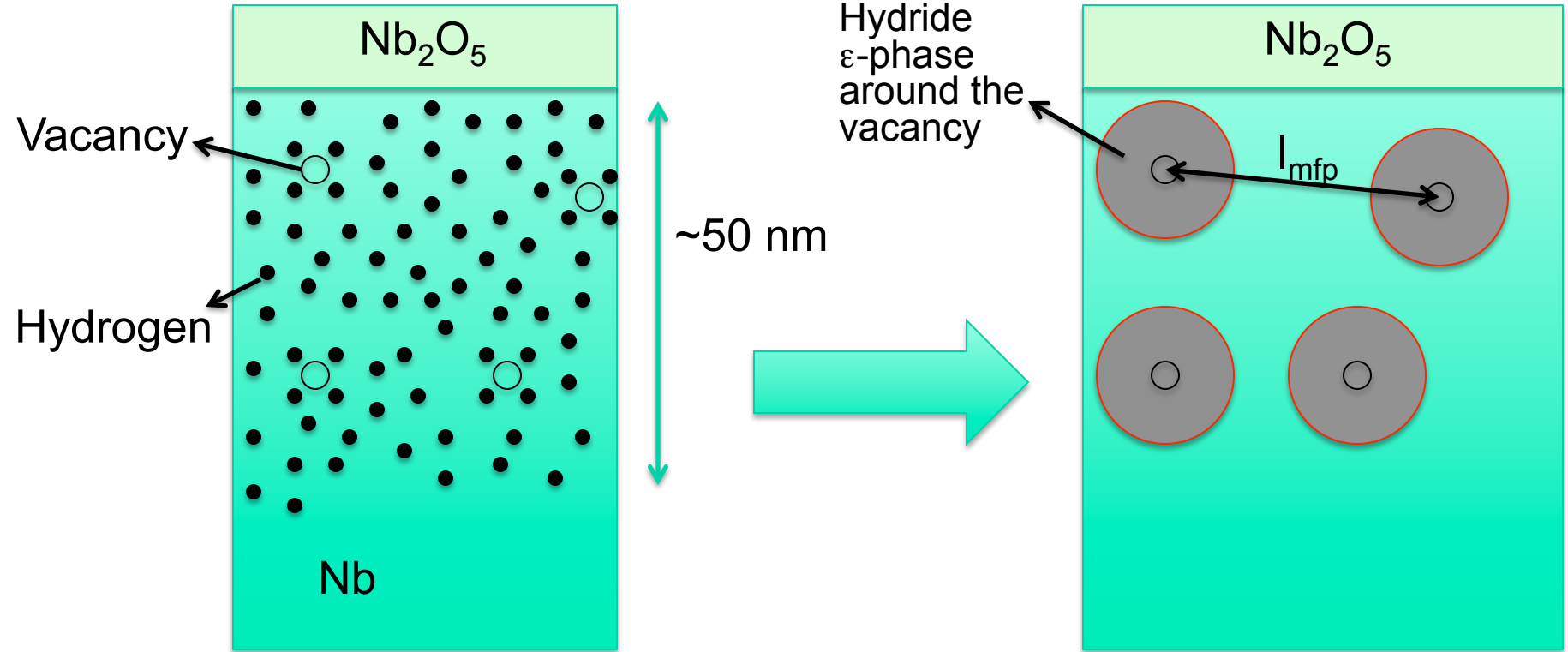
All H will precipitate into hydrides within the layer L if nucleation centers exist



For slow cooldown $L > 3 \text{ mm}$ allowing to collect H from all the wall thickness. This (bulk supply) can be changed by $600\text{-}800^\circ\text{C}$ making not enough H to form large hydrides (Q-disease)

T = 300 K

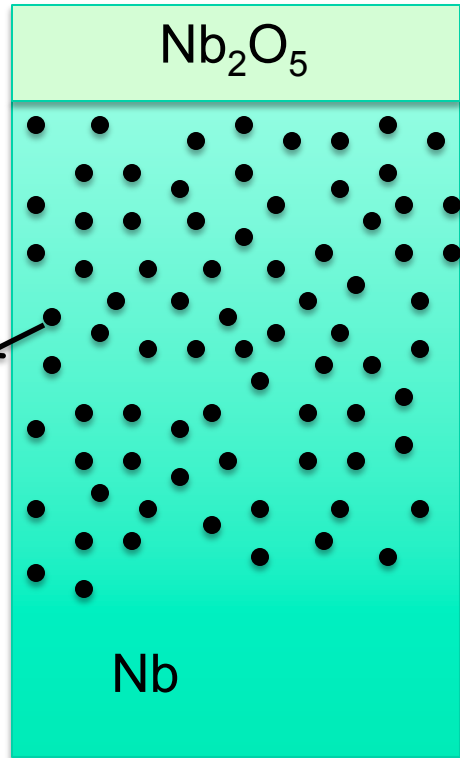
T = 2 K



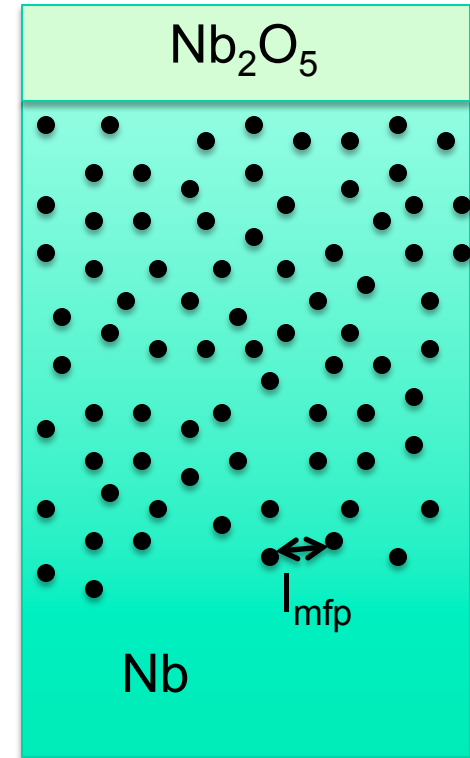
Mean free path increases – determined by Hydride-Hydride distance

T = 300 K

T = 2 K

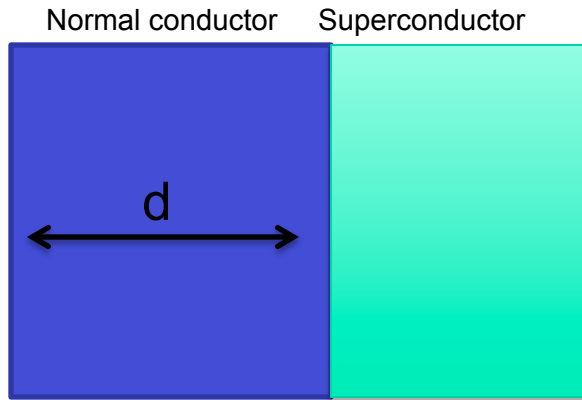


~50 nm



Mean free path stays low – determined by H-H distance

- Model does not require diffusion of any impurities during 120C - only vacancies
 - Near-surface vacancies diffuse to sinks and annihilate during 120C
 - Presence/absence of vacancy-H complexes as nucleation centers for hydrides matters for the precipitation state



A. Fauchere and G. Blatter, Phys. Rev. B, 56, 21 (1997)

$$H_b(T=0) \approx \frac{1}{6} \frac{\Phi_0}{\lambda_N d}$$

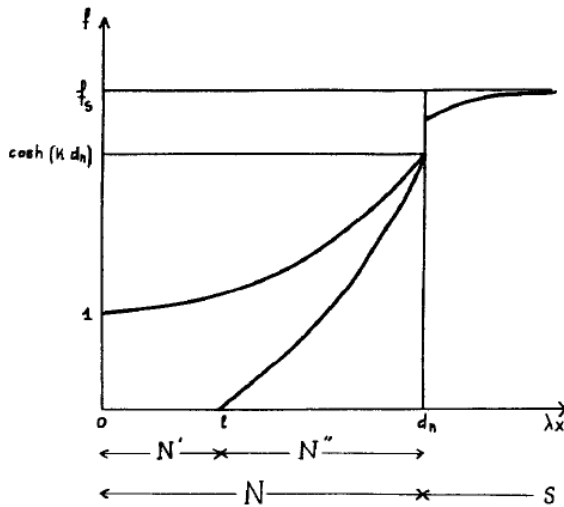
$$H_b(T \gg T_A) \approx \frac{\sqrt{2}}{\pi} \gamma(T, \Delta) \frac{\Phi_0}{\lambda_N d} e^{-d/\xi_N(T)}$$

$$\xi_N = \frac{\hbar v_F}{2\pi kT} \quad T_A = \frac{\hbar v_F}{2\pi k d}$$

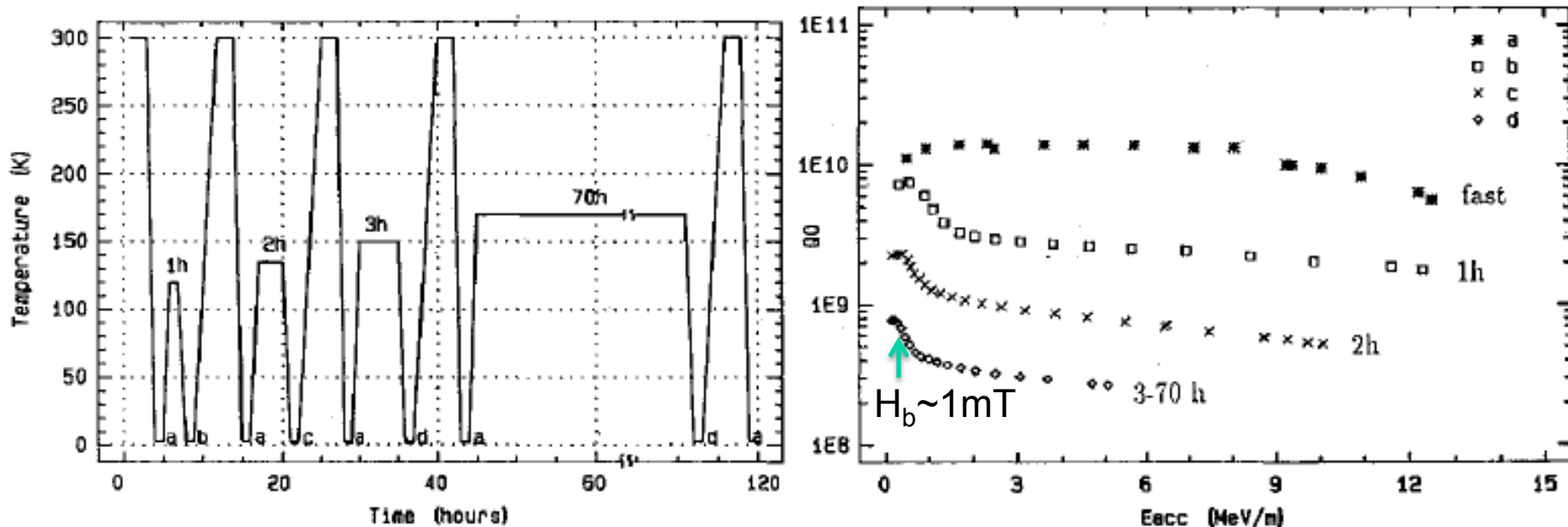
$\xi_N \approx 800 \text{ nm}$ for Nb at $T = 2\text{K}$

If $d = 10 \text{ nm} \Rightarrow T_A = 166 \text{ K}$, $T \ll T_A$

At $H > H_b$ – no Meissner screening – proximity-induced SC is destroyed

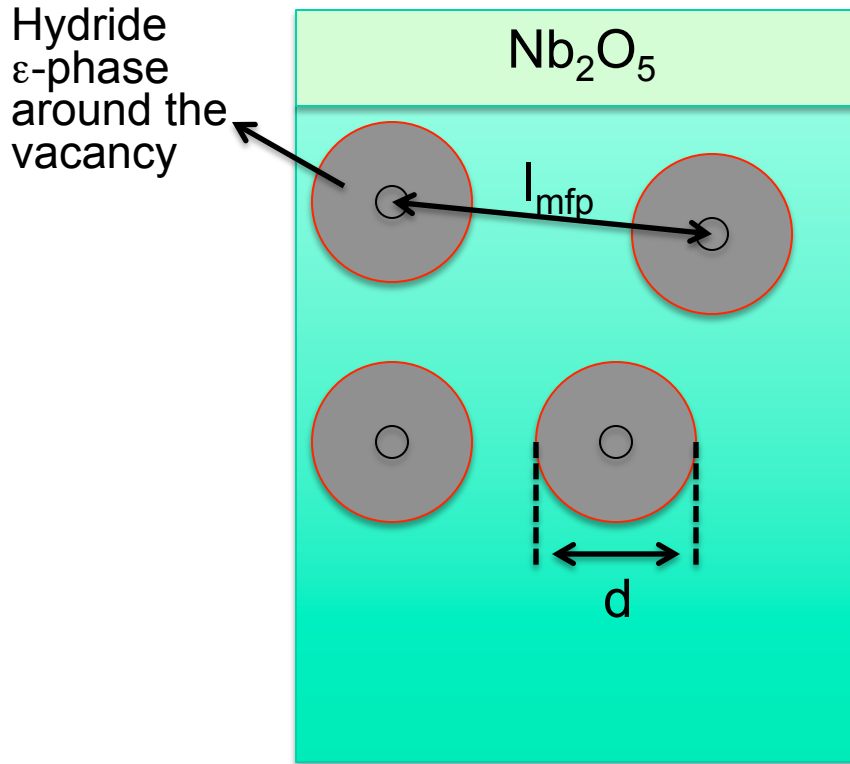


De Gennes and Hurault, Phys. Lett. 17, 3 (1965)

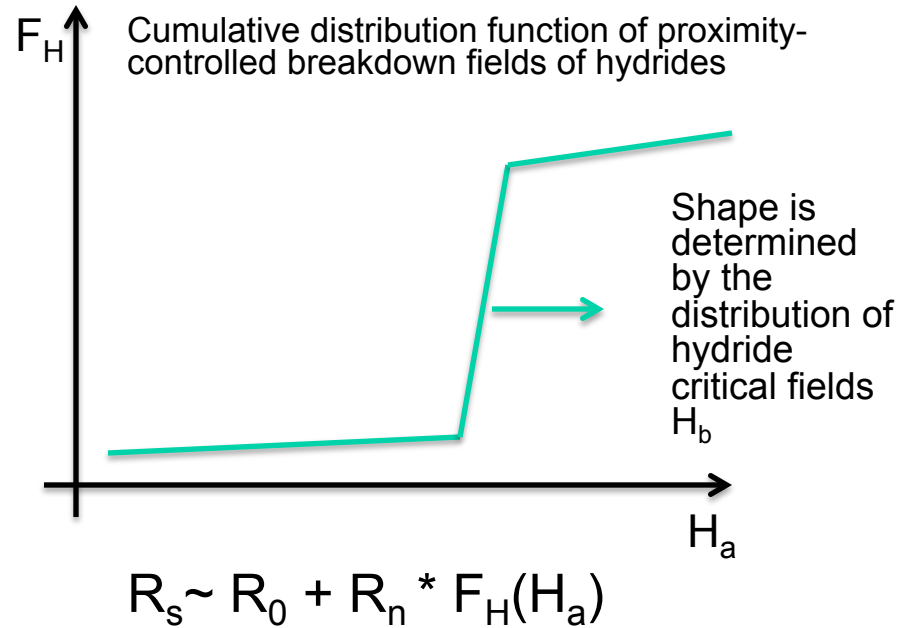


Aune et al., LINAC'90

- From our experiments with hydrides (see SRF Materials 2012 talk)
 - $d \sim 100 \text{ nm}$ (150 K hold) \Rightarrow
 - $d \sim 100 \text{ nm} \Leftrightarrow H_b \sim 1 \text{ mT}$
 - \Rightarrow in the limit of $T \ll T_A$ if $H_b = 100 \text{ mT} \Rightarrow d \sim 1 \text{ nm}$

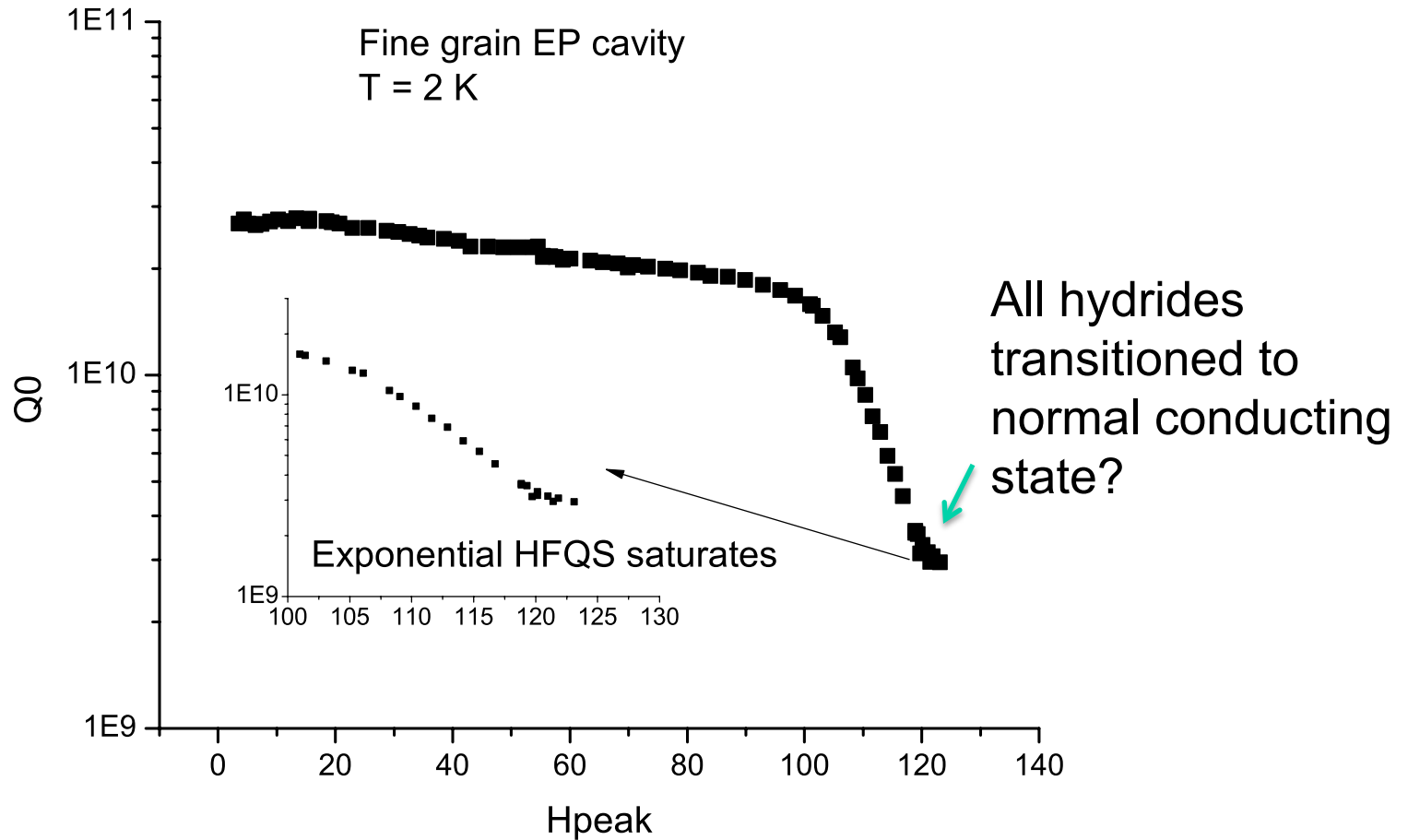


- Nanohydrides lose proximity-induced superconductivity completely => HFQS
- Change of order parameter $\Delta(z)$ with field at $H < H_b \rightarrow$ MFQS?



We can obtain $F_H(H_a)$ from the distribution of diameters d since $H_b = H_b(d)$:
 (i.e. if $H_b \sim 1/d$ at $T \ll T_A$)

- Saturation of the HFQS at higher fields (similar to Q-disease)
 - Need more RF power to check (preliminary data next slide)
- Introduce vacancies into baked cavity should recreate locally high field Q-slope
 - Irradiation experiments on the cavity to be done soon
- Small hydrides should be observed directly at $T < \sim 150\text{K}$
 - TEM ongoing
 - Small angle X-ray scattering scheduled



- Positron annihilation data suggests major role of vacancies in the 120C baking effect
- Precipitation of hydrides within surface layer may explain the mean free path effect of 120C bake
 - Without involving any impurity diffusion
- Nanohydrides must be present in the RF layer of SRF cavities if nucleation centers exist
 - There is always enough H and time during cooldown
- Proximity effect on nanohydrides can explain the high field Q-slope
- Is medium field Q-slope also a consequence of proximity on hydrides?
 - Or on suboxides?

- A. Grassellino, F. Barkov, Y. Trenikhina, L. Cooley – FNAL
- H. Padamsee - Cornell